

Application No.: 10/601,597Docket No.: 2336-181**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:**1-4. (canceled)**

5. **(currently amended) A GaN light emitting diode, comprising:**
a first conductive GaN clad layer with an upper surface provided with a first contact formed
thereon;

an active layer formed on a lower surface of the first conductive GaN clad layer;
a second conductive GaN clad layer formed on a lower surface of the active layer;
a conductive adhesive layer formed on the second conductive GaN clad layer; and
a conductive substrate, with a lower surface provided with a second contact formed thereon,
formed on a lower surface of the conductive adhesive layer;

The GaN light emitting diode as set forth in claim 1, wherein the conductive adhesive layer
is made of a material selected from the group consisting of Au-Sn, Sn, In, Au-Ag and Pb-Sn.

6-17. (canceled)

18. **(new) The diode of claim 5, wherein the conductive adhesive layer is made of an**
Au-Sn alloy.

19. **(new) The diode of claim 5, wherein the conductive adhesive layer is made of Sn.**

Application No.: 10/601,597

Docket No.: 2336-181

20. (new) The diode of claim 5, wherein the conductive adhesive layer is made of In.
21. (new) The diode of claim 5, wherein the conductive adhesive layer is made of an Au-Ag alloy.
22. (new) The diode of claim 5, wherein the conductive adhesive layer is made of an Pb-Sn alloy.
23. (new) The diode of claim 5, wherein the conductive adhesive layer is a reflective layer made of a material selected from the group consisting of Au-Sn, Sn, In, and Au-Ag.